ABSTRACT

INTERCONNECT CAPPING LAYER AND METHOD OF FABRICATION

The present invention relates to an interconnect capping layer and a method of fabricating a capping layer for an interconnect. In particular, but not exclusively, the invention relates to a capping layer for a copper interconnect used to interconnect elements in an integrated circuit. Embodiments of the invention provide a method of fabricating a capping layer for an interconnect in an integrated circuit, comprising the steps of: forming an interconnect comprising upper and lower lateral surfaces; forming a lateral diffusion stop layer between said lateral surfaces; and forming a capping layer.

Fig. 3